

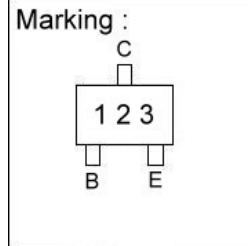
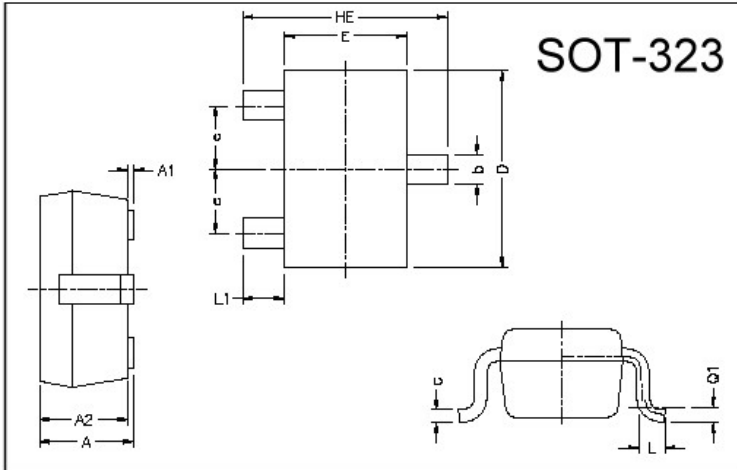
GS123

NPN EPITAXIAL TRANSISTOR

Description

The GS123 is designed for general purpose amplifier applications.

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

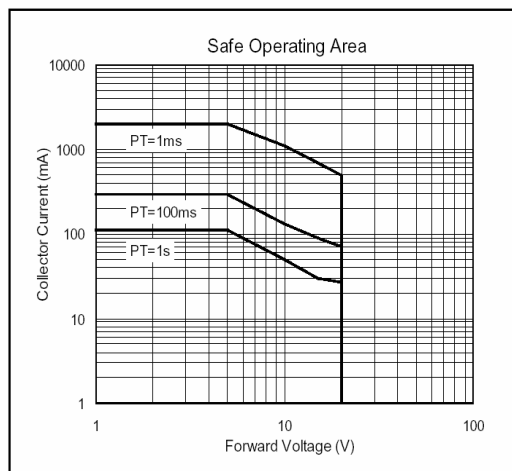
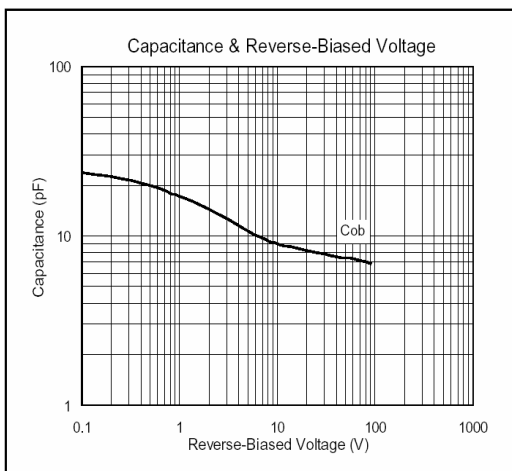
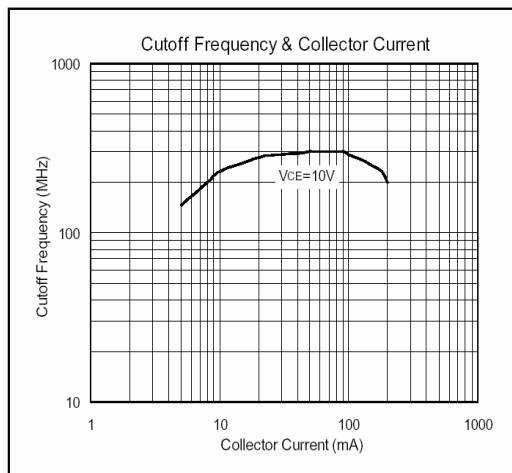
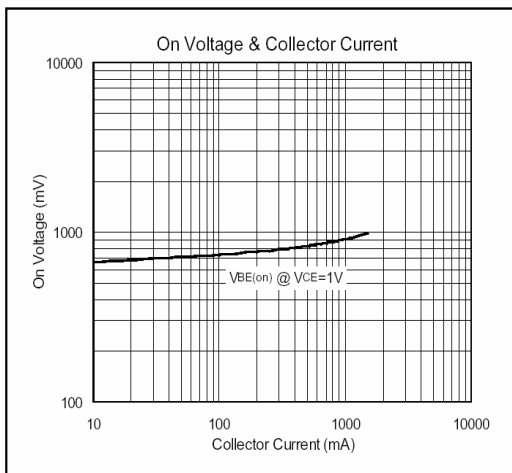
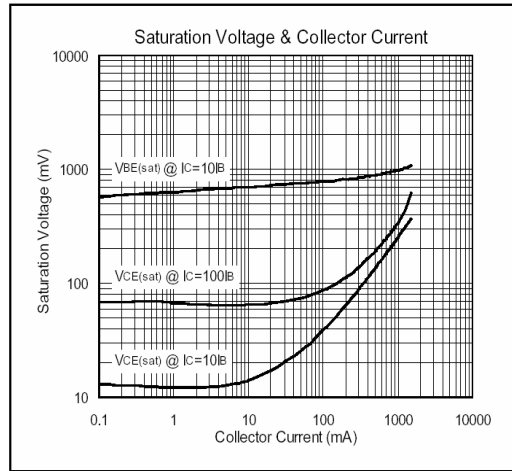
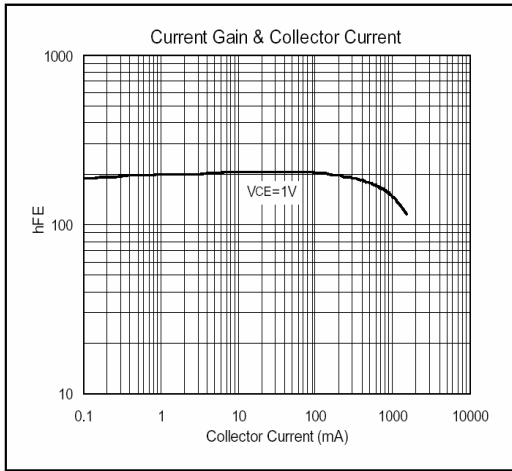
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	VCBO	25	V
Collector to Emitter Voltage	VCEO	20	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	I _C	700	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	25	-	-	V	I _C =10μA, I _E =0
BVCEO	20	-	-	V	I _C =1mA, I _B =0
BVEBO	5	-	-	V	I _E =10μA, I _C =0
ICBO	-	-	1	μA	V _{CB} =20V, I _E =0
VCE(sat)	-	-	400	mV	I _C =500mA, I _B =50mA
VBE(on)	-	-	1	V	V _{CE} =1V, I _C =150mA
hFE	150	-	300		V _{CE} =1V, I _C =150mA
f _T	150	-	-	MHz	V _{CE} =10V, I _C =20mA, f=100MHz
C _{ob}	-	-	10	pF	V _{CB} =10V, f=1MHz

Characteristics Curve



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Head Office And Factory:

- Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165